

ADG704—SPECIFICATIONS¹ ($V_{DD} = +5\text{ V} \pm 10\%$, $GND = 0\text{ V}$. All Specifications -40°C to $+85^{\circ}\text{C}$, unless otherwise noted.)

Parameter	B Version		Units	Test Conditions/Comments
	+25°C	−40°C to +85°C		
ANALOG SWITCH				
Analog Signal Range		0 V to V _{DD}	V	
On-Resistance (R _{ON})	2.5		Ω typ	V _S = 0 V to V _{DD} , I _{DS} = −10 mA; Test Circuit 1
	4	4.5	Ω max	
On-Resistance Match Between Channels (ΔR _{ON})		0.1	Ω typ	V _S = 0 V to V _{DD} , I _{DS} = −10 mA
		0.4	Ω max	
On-Resistance Flatness (R _{FLAT(ON)})	0.75		Ω typ	V _S = 0 V to V _{DD} , I _{DS} = −10 mA
		1.2	Ω max	
LEAKAGE CURRENTS				
Source OFF Leakage I _S (OFF)	±0.01		nA typ	V _{DD} = +5.5 V V _S = 4.5 V/1 V, V _D = 1 V/4.5 V; Test Circuit 2
	±0.1	±0.3	nA max	
Drain OFF Leakage I _D (OFF)	±0.01		nA typ	V _S = 4.5 V/1 V, V _D = 1 V/4.5 V; Test Circuit 2
	±0.1	±0.3	nA max	
Channel ON Leakage I _D , I _S (ON)	±0.01		nA typ	V _S = V _D = 4.5 V or 1 V; Test Circuit 3
	±0.1	±0.3	nA max	
DIGITAL INPUTS				
Input High Voltage, V _{INH}		2.4	V min	
Input Low Voltage, V _{INL}		0.8	V max	
Input Current				
I _{INL} or I _{INH}	0.005		μA typ	V _{IN} = V _{INL} or V _{INH}
		±0.1	μA max	
DYNAMIC CHARACTERISTICS ²				
t _{ON}	14		ns typ	R _L = 300 Ω, C _L = 35 pF
		20	ns max	V _S = 3 V, Test Circuit 4
t _{OFF}	6		ns typ	R _L = 300 Ω, C _L = 35 pF
		13	ns max	V _S = 3 V, Test Circuit 4
Break-Before-Make Time Delay, t _D	8		ns typ	R _L = 300 Ω, C _L = 35 pF
		1	ns min	V _{S1} = V _{S2} = 3 V, Test Circuit 5
Charge Injection	3		pC typ	V _S = 2 V, R _S = 0 Ω, C _L = 1 nF; Test Circuit 6
Off Isolation	−60		dB typ	R _L = 50 Ω, C _L = 5 pF, f = 10 MHz
	−80		dB typ	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz; Test Circuit 7
Channel-to-Channel Crosstalk	−62		dB typ	R _L = 50 Ω, C _L = 5 pF, f = 10 MHz
	−82		dB typ	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz; Test Circuit 8
Bandwidth −3 dB	200		MHz typ	R _L = 50 Ω, C _L = 5 pF; Test Circuit 9
C _S (OFF)	9		pF typ	
C _D (OFF)	37		pF typ	
C _D , C _S (ON)	54		pF typ	
POWER REQUIREMENTS				
I _{DD}	0.001		μA typ	V _{DD} = +5.5 V Digital Inputs = 0 V or 5 V
		1.0	μA max	

NOTES

¹Temperature ranges are as follows: B Version: -40°C to $+85^{\circ}\text{C}$.

²Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

SPECIFICATIONS¹ ($V_{DD} = +3\text{ V} \pm 10\%$, $GND = 0\text{ V}$. All Specifications -40°C to $+85^{\circ}\text{C}$, unless otherwise noted.)

Parameter	B Version		Units	Test Conditions/Comments
	+25°C	−40°C to +85°C		
ANALOG SWITCH				
Analog Signal Range	4.5	0 V to V _{DD}	V	V _S = 0 V to V _{DD} , I _{DS} = −10 mA; Test Circuit 1
On-Resistance (R _{ON})		5	Ω typ	
		8	Ω max	
On-Resistance Match Between Channels (ΔR _{ON})	0.1		Ω typ	V _S = 0 V to V _{DD} , I _{DS} = −10 mA
		0.4	Ω max	
On-Resistance Flatness (R _{FLAT(ON)})		2.5	Ω typ	V _S = 0 V to V _{DD} , I _{DS} = −10 mA
LEAKAGE CURRENTS				
Source OFF Leakage I _S (OFF)	±0.01		nA typ	V _{DD} = +3.3 V
	±0.1	±0.3	nA max	V _S = 3 V/1 V, V _D = 1 V/3 V; Test Circuit 2
Drain OFF Leakage I _D (OFF)	±0.01		nA typ	V _S = 3 V/1 V, V _D = 1 V/3 V;
	±0.1	±0.3	nA max	Test Circuit 2
Channel ON Leakage I _D , I _S (ON)	±0.01		nA typ	V _S = V _D = 3 V or 1 V;
	±0.1	±0.3	nA max	Test Circuit 3
DIGITAL INPUTS				
Input High Voltage, V _{INH}		2.0	V min	V _{IN} = V _{INL} or V _{INH}
Input Low Voltage, V _{INL}		0.4	V max	
Input Current	0.005			
I _{INL} or I _{INH}		±0.1	μA typ μA max	
DYNAMIC CHARACTERISTICS ²				
t _{ON}	16		ns typ	R _L = 300 Ω, C _L = 35 pF V _S = 2 V, Test Circuit 4
		24	ns max	
t _{OFF}	8		ns typ	R _L = 300 Ω, C _L = 35 pF V _S = 2 V, Test Circuit 4
		16	ns max	
Break-Before-Make Time Delay, t _D	9		ns typ	R _L = 300 Ω, C _L = 35 pF V _{S1} = V _{S2} = 2 V, Test Circuit 5
		1	ns min	
Charge Injection	3		pC typ	V _S = 1.5 V, R _S = 0 Ω, C _L = 1 nF; Test Circuit 6
Off Isolation	−60		dB typ	R _L = 50 Ω, C _L = 5 pF, f = 10 MHz R _L = 50 Ω, C _L = 5 pF, f = 1 MHz; Test Circuit 7
	−80		dB typ	
Channel-to-Channel Crosstalk	−62		dB typ	R _L = 50 Ω, C _L = 5 pF, f = 10 MHz R _L = 50 Ω, C _L = 5 pF, f = 1 MHz; Test Circuit 8
	−82		dB typ	
Bandwidth −3 dB	200		MHz typ	R _L = 50 Ω, C _L = 5 pF; Test Circuit 9
C _S (OFF)	9		pF typ	
C _D (OFF)	37		pF typ	
C _D , C _S (ON)	54		pF typ	
POWER REQUIREMENTS				
I _{DD}	0.001		μA typ	V _{DD} = +3.3 V Digital Inputs = 0 V or 3 V
		1.0	μA max	

NOTES

¹Temperature ranges are as follows: B Version: -40°C to $+85^{\circ}\text{C}$.²Guaranteed by design, not subject to production test.

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ABSOLUTE MAXIMUM RATINGS¹

(T_A = +25°C unless otherwise noted)

V _{DD} to GND	−0.3 V to +6 V
Analog, Digital Inputs ²	−0.3 V to V _{DD} + 0.3 V or 30 mA, Whichever Occurs First
Continuous Current, S or D	30 mA
Peak Current, S or D	100 mA (Pulsed at 1 ms, 10% Duty Cycle Max)
Operating Temperature Range	
Industrial (B Version)	−40°C to +85°C
Storage Temperature Range	−65°C to +150°C
Junction Temperature	+150°C
μSOIC Package, Power Dissipation	315 mW
θ _{JA} Thermal Impedance	206°C/W
Lead Temperature, Soldering	
Vapor Phase (60 sec)	+215°C
Infrared (15 sec)	+220°C
ESD	2 kV

NOTES

¹Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.

²Overvoltages at IN, S or D will be clamped by internal diodes. Current should be limited to the maximum ratings given.

ORDERING GUIDE

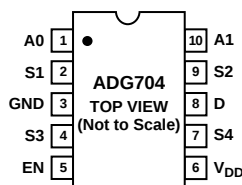
Model	Temperature Range	Brand ¹	Package Option ²
ADG704BRM	−40°C to +85°C	S9B	RM-10

NOTES

¹Brand = Due to small package size, these three characters represent the part number.

²RM = μSOIC.

PIN CONFIGURATION (10-Lead μSOIC)



TERMINOLOGY

V _{DD}	Most positive power supply potential.
GND	Ground (0 V) reference.
S	Source terminal. May be an input or output.
D	Drain terminal. May be an input or output.
A0, A1	Logic control inputs.
EN	Logic control input.
R _{ON}	Ohmic resistance between D and S.
ΔR _{ON}	On resistance match between any two channels i.e., R _{ONmax} −R _{ONmin} .
R _{FLAT(ON)}	Flatness is defined as the difference between the maximum and minimum value of on resistance as measured over the specified analog signal range.
I _D (OFF)	Drain leakage current with the switch “OFF.”
I _S (OFF)	Source leakage current with the switch “OFF.”
I _D , I _S (ON)	Channel leakage current with the switch “ON.”
V _D (V _S)	Analog voltage on terminals D, S.
C _S (OFF)	“OFF” switch source capacitance.
C _D (OFF)	“OFF” switch drain capacitance.
C _D , C _S (ON)	“ON” switch capacitance.
t _{ON}	Delay between applying the digital control input and the output switching on. See Test Circuit 4.
t _{OFF}	Delay between applying the digital control input and the output switching off.
t _D	“OFF” time or “ON” time measured between the 90% points of both switches, when switching from one address state to another. See Test Circuit 5.
Crosstalk	A measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance.
Off Isolation	A measure of unwanted signal coupling through an “OFF” switch.
Charge Injection	A measure of the glitch impulse transferred from the digital input to the analog output during switching.
Bandwidth	The frequency at which the output is attenuated by −3 dBs.
On Response	The frequency response of the “ON” switch.
On Loss	The voltage drop across the “ON” switch, seen on the On Response vs. Frequency plot as how many dBs the signal is away from 0 dB at very low frequencies.

Table I. Truth Table

A1	A0	EN	ON Switch
X	X	0	NONE
0	0	1	1
0	1	1	2
1	0	1	3
1	1	1	4

CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the ADG704 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



Typical Performance Characteristics—ADG704

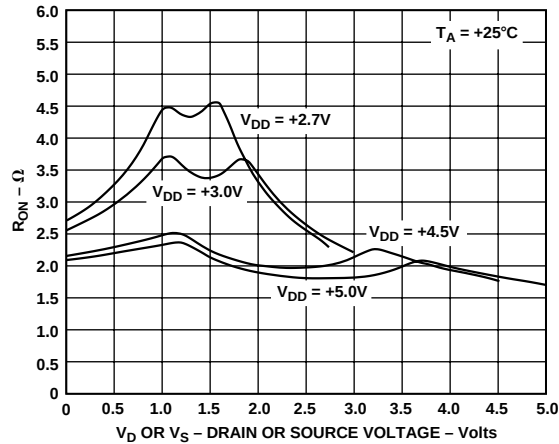


Figure 1. On Resistance as a Function of V_D (V_S) Single Supplies

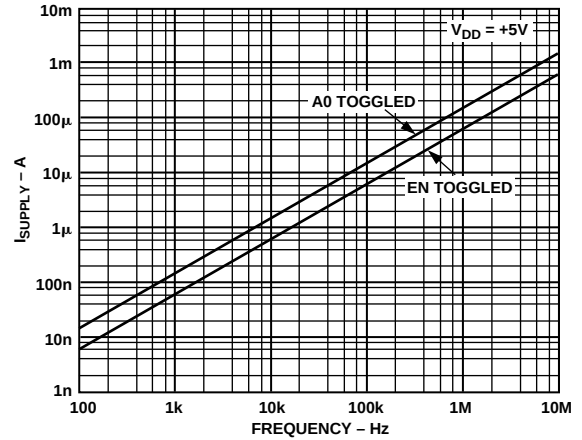


Figure 4. Supply Current vs. Input Switching Frequency

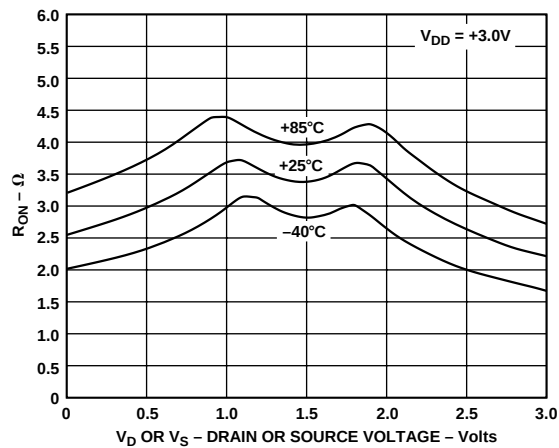


Figure 2. On Resistance as a Function of V_D (V_S) for Different Temperatures; $V_{DD} = 3\text{ V}$

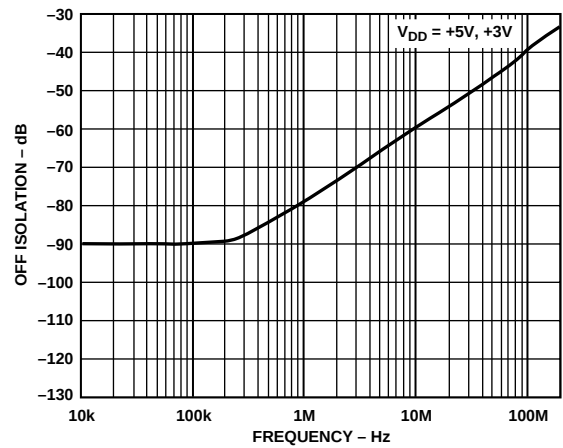


Figure 5. Off Isolation vs. Frequency

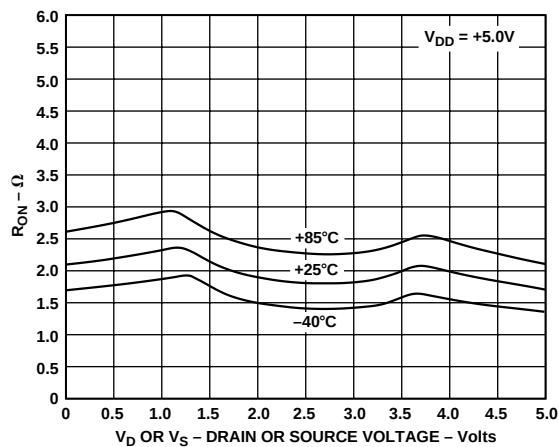


Figure 3. On Resistance as a Function of V_D (V_S) for Different Temperatures; $V_{DD} = 5\text{ V}$

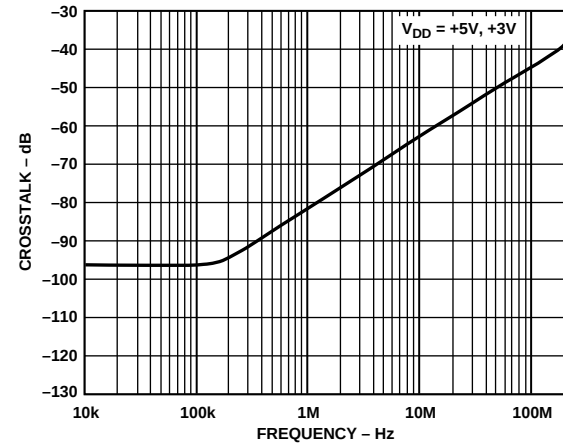


Figure 6. Crosstalk vs. Frequency

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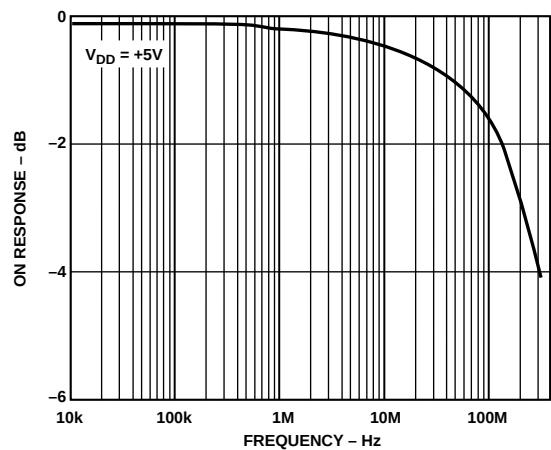


Figure 7. On Response vs. Frequency

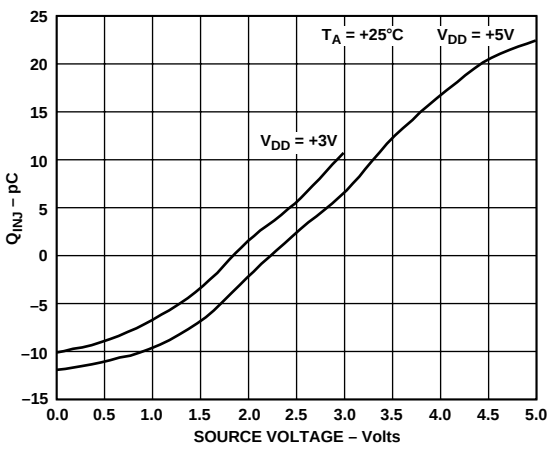


Figure 8. Charge Injection vs. Source Voltage

APPLICATIONS

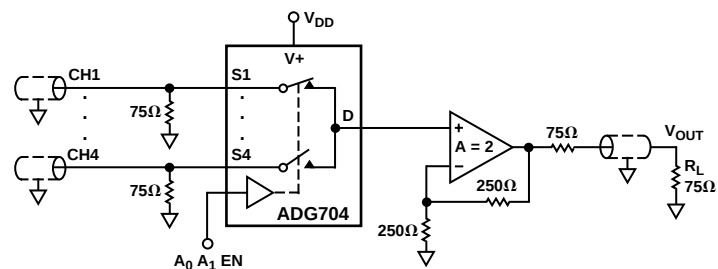
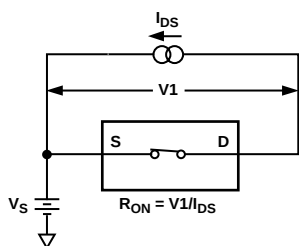
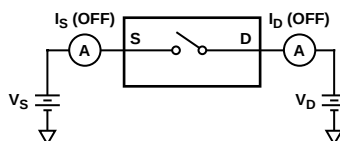


Figure 9. 4-Channel Video Multiplexing

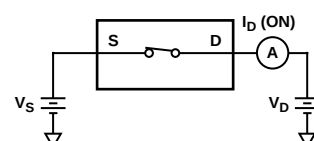
Test Circuits



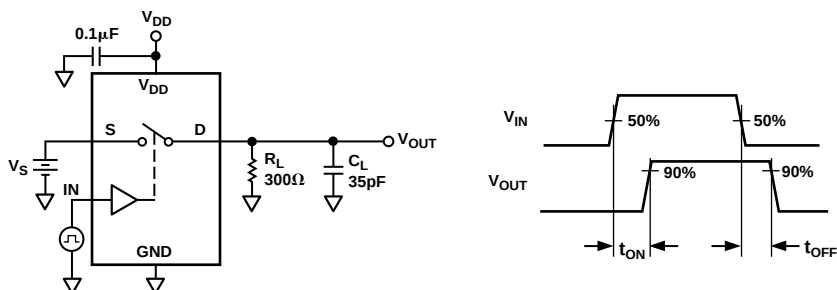
Test Circuit 1. On Resistance



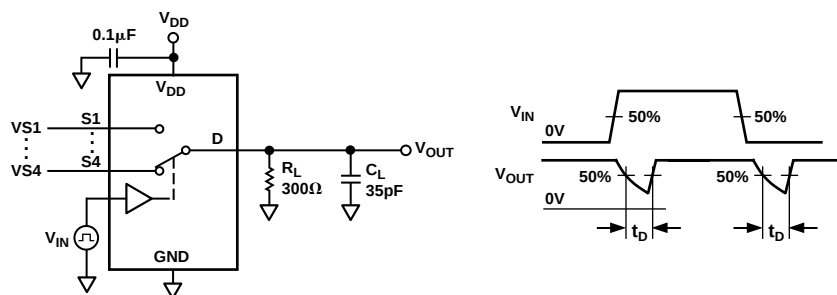
Test Circuit 2. Off Leakage



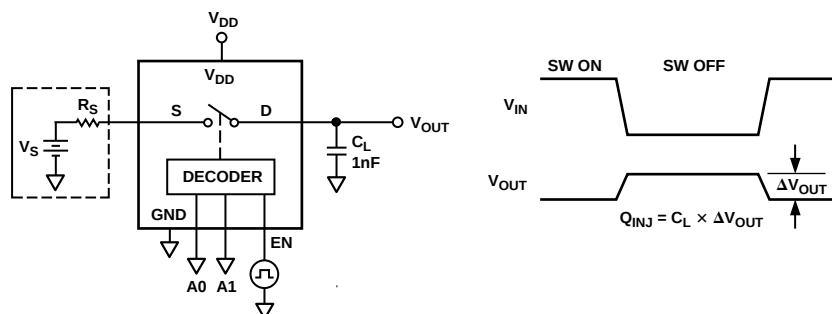
Test Circuit 3. On Leakage



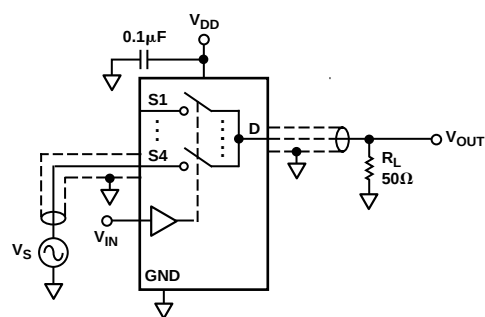
Test Circuit 4. Switching Times



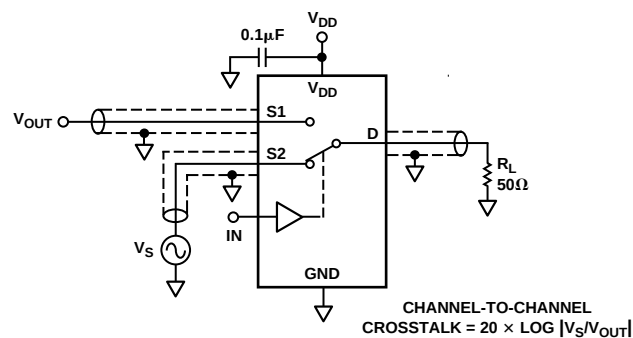
Test Circuit 5. Break-Before-Make Time Delay, t_D



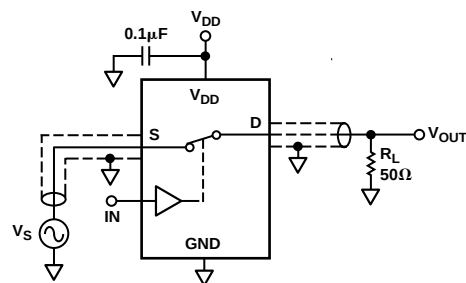
Test Circuit 6. Charge Injection



Test Circuit 7. Off Isolation



Test Circuit 8. Channel-to-Channel Crosstalk



Test Circuit 9. Bandwidth

OUTLINE DIMENSIONS

Dimensions shown in inches and (mm).

10-Lead μ SOIC
(RM-10)

